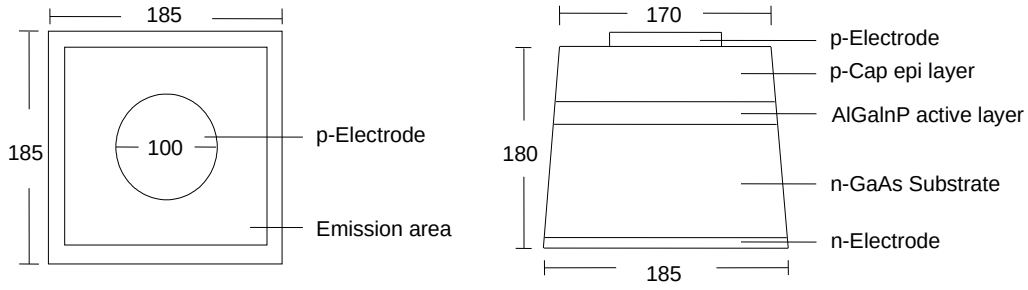
Features :

- MOVPE Epi Wafer
- Suitable for New Creative Products

Typical Applications :

- Dot Matrix
- Lamp Display
- High Performance X'mas Lamps

Outline Dimensions : (Unit: um)



Physical Structure :

Chip dimension	Chip size	185 um x 185 um
	Thickness	180 um
	Emission area	170 um
	Bonding pad	100 um
Electrode	Top: P (anode)	Aluminum (Gold optional)
	Backside: N (cathode)	Gold alloy
Surface condition	Not frosted	

Electro-Optical Characteristics : (Ta = 25℃)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	I_F = 20 mA	-	2.15	2.40	V
Reverse Voltage	V_R	I_R = 10 uA	5	-	-	V
Wavelength	λ_p	I_F = 20 mA	-	573	-	nm
	λ_D		568	573	576	
Spectral width at half height	$\triangle\lambda$	I_F = 20 mA	-	20	-	nm
Luminous Intensity	I_V	I_F = 20 mA	20	-	-	mcd
			25			mcd

Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. Forward Voltage

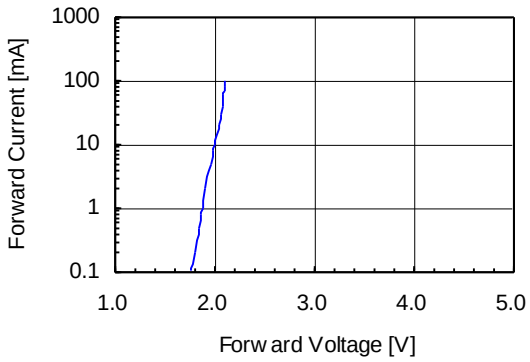


Fig 2. Relative Intensity vs. Forward Current

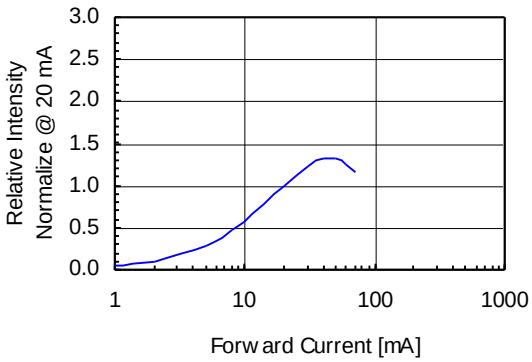


Fig 3. Forward Voltage vs. Temperature

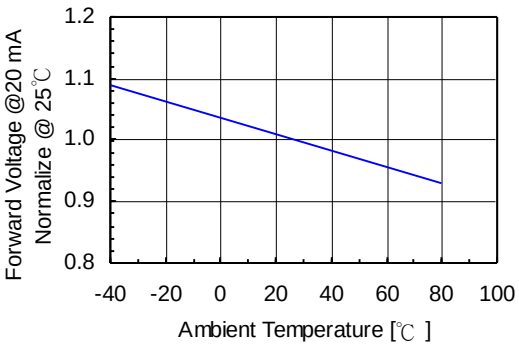


Fig 4. Relative Intensity vs. Temperature

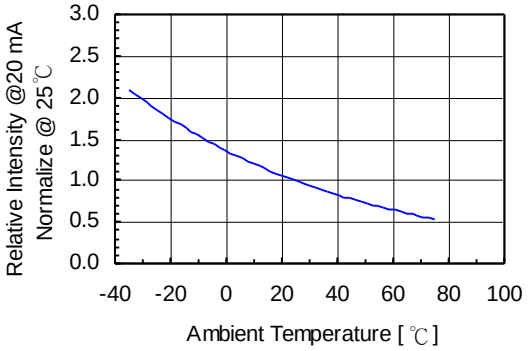


Fig 5. Relative Intensity vs. Wavelength